

## CLAIMS

1. A photolithographic method comprising forming overlapping exposure patterns on a photosensitive material from light passed through a single reticle; the reticle being displaced relative to the photosensitive material between a first exposure to a first light and a second exposure to a second light so that a first pattern of the first light produced by the first exposure is offset and overlapping on the photosensitive material relative to a second pattern of the second light produced by the second exposure.
2. The method of claim 1 wherein the displacement of the reticle relative to the photosensitive material comprises movement of the reticle while the photosensitive material is held stationary.
3. The method of claim 1 wherein the displacement of the reticle relative to the photosensitive material comprises movement of the photosensitive material while the reticle is held stationary.
4. The method of claim 1 wherein the displacement of the reticle relative to the photosensitive material comprises movement of both the photosensitive material and the reticle relative to one another.

5. The method of claim 1 wherein the first light has a different wavelength than the second light.

6. The method of claim 1 wherein the first light has the same wavelength as the second light.

7. The method of claim 1 wherein the photosensitive material is over a semiconductive substrate, and wherein at least portions of the combined first and second patterns define portions of capacitor structures; the method further comprising:

selectively removing either the exposed or unexposed portions of the photosensitive material to pattern the photosensitive material into blocks comprising an outline of the portions of the capacitor structures; and

transferring the outline to at least a portion of the semiconductive substrate underlying the photosensitive material to form the portions of the capacitor structures.

8. The method of claim 1 wherein the photosensitive material is over a semiconductive substrate, and wherein at least portions of the combined first and second patterns define portions of DRAM structures; the method further comprising:

selectively removing either the exposed or unexposed portions of the photosensitive material to pattern the photosensitive material into blocks comprising an outline of the portions of the DRAM structures; and

transferring the outline to at least a portion of the semiconductive substrate underlying the photosensitive material to form the portions of the DRAM structures.

9. A photolithographic method comprising forming overlapping first and second exposure patterns on a photosensitive material from electromagnetic radiation passed through a single reticle; wherein the first exposure pattern of the radiation comprises features separated by about a minimum feature spacing that can be accomplished with a single reticle exposure during the photolithographic processing; and wherein the overlapping first and second patterns comprise features separated by less than said minimum feature spacing.

10. The method of claim 9 wherein at least 20% of the second exposure pattern overlaps the first exposure pattern.

11. The method of claim 9 wherein at least 30% of the second exposure pattern overlaps the first exposure pattern.

12. The method of claim 9 wherein from at least about 20% to about 80% of the second exposure pattern overlaps the first exposure pattern.

13. The method of claim 9 wherein from at least about 20% to about 50% of the second exposure pattern overlaps the first exposure pattern.

14. The method of claim 9 wherein the photosensitive material is over a semiconductive substrate, and wherein at least portions of the combined first and second patterns define portions of semiconductor device structures; the method further comprising:

selectively removing either the exposed or unexposed portions of the photosensitive material to pattern the photosensitive material into blocks comprising an outline of the portions of the semiconductor device structures; and

transferring the outline to at least a portion of the semiconductive substrate underlying the photosensitive material to form the portions of the semiconductor device structures.

15. The method of claim 9 wherein the photosensitive material is over a semiconductive substrate, and wherein at least portions of the combined first and second patterns define portions of capacitor structures; the method further comprising:

selectively removing either the exposed or unexposed portions of the photosensitive material to pattern the photosensitive material into blocks comprising an outline of the portions of the capacitor structures; and

transferring the outline to at least a portion of the semiconductive substrate underlying the photosensitive material to form the portions of the capacitor structures.

16. A photolithographic method comprising:

providing a semiconductor substrate having a photosensitive material thereover;

passing electromagnetic radiation through a reticle to form a first pattern of the radiation on the photosensitive material; the reticle having a first dimension along a first axis;

displacing the reticle relative to the semiconductor substrate along the first axis by an increment less than the first dimension of the reticle; and

after the displacing, passing the electromagnetic radiation through the reticle to form a second pattern of the radiation on the photosensitive material.

17. The method of claim 16 wherein the reticle comprises a first portion that defines that first pattern and second portion which is opaque to the radiation; the second portion having an area that is at least about 20% of the area of the reticle.

18. The method of claim 16 wherein the reticle comprises a first portion that defines that first pattern and second portion which is opaque to the radiation; the second portion having an area that is at least about 30% of the area of the reticle.

19. The method of claim 16 wherein the reticle comprises a first portion that defines that first pattern and second portion which is opaque to the radiation; the first portion being about equal in area to the second portion.

20. The method of claim 16 wherein the reticle has a second dimension along a second axis; the second axis being orthogonal to the first axis, the method further comprising:

displacing the reticle relative to the semiconductor substrate along the second axis by an increment less than the second dimension of the reticle; and

after displacing the reticle along the second axis, passing the radiation through the reticle to form another pattern of the radiation on the photosensitive material.

21. The method of claim 20 wherein the displacing the reticle along the second axis occurs before the displacing the reticle along the first axis.

22. The method of claim 20 wherein the displacing the reticle along the second axis occurs after the forming the second pattern of the radiation on the photosensitive material.

23. The method of claim 16 wherein the first pattern of the radiation comprises features separated by about a minimum feature spacing that can be accomplished with a single reticle exposure at the time of the photolithographic processing; and wherein the overlapping first and second patterns comprise features separated by less than said minimum feature spacing.

24. The method of claim 16 wherein the first pattern of the radiation consists of a unit feature which is repeated a plurality of times across the pattern.

25. The method of claim 16 wherein the first pattern of the radiation comprises a first unit feature which is repeated a plurality of times across the pattern, and a second unit feature which is not repeated across the pattern.

26. The method of claim 16 wherein the first pattern of the radiation comprises first and second features; and wherein the first features are repeated in the first pattern more frequently than any repeating of the second features in the first pattern.